A Bibliography of Publications of William M. Coughran

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Abstract

This bibliography records publications of William M. Coughran.

Title word cross-reference

C_2H_4 [CRSM73]. *IV* [CFS94]. N_2 [CRSM73].

/ [Boi97].

Adaptive [BCF91, CS90, CPS91]. **Advanced** [BDR+94]. **Algorithm** [CH81]. **Algorithms** [BBC+90, CJ90, CGP+92b, CFS94]. **Alternate** [BCCS89]. **Alternate-Block-Factorization** [BCCS89]. **Analysis** [BCC+79, Cou77, CGR87, CJ90]. **Analyzer** [CGR83]. **Animation** [CG90c]. **Applied** [BCG94a, BCG94b]. **Approach** [LFC90]. **Approximate** [Cou80]. **Aspects** [BCF+86, CGR87, SCF+86]. **assessment** [Boi97]. **Augmented** [CFS94].

based [BGP+92, Cou97]. **Bénard** [BCG+84, GCS82, GC84]. **BiCMOS** [PBR+92]. **Bifurcations** [CGP92a]. **Bipolar** [PBR+92]. **Block** [BCCS89]. **Boundary** [Cou80, Cou84, Cou85].

CAzM [CGR83, CEK+89]. **Cell** [GCC88]. **Challenges** [SC94]. **Chaos** [GCC88]. **Characteristics** [CGP92a]. **Characterization** [PBR+92]. **Charges** [CFG89]. **Circuit** [BDR+94, CGR83, CGR87, CFS94, LFC90]. **Circuit-Analyzer** [CGR83]. **Circuits** [BCF+85]. **CMOS** [CPS88]. **CO** [CRSM73]. **Collaboration** [CEK+89]. **Combined** [BDR+94]. **Complete** [CH81]. **computation** [Cou97]. **Computational** [BCF+86, CGR87, CPS88, CGP+92b, SC94]. **Computing** [CG89, CGP92a]. **Concerning** [Cou77]. **Conditions** [Cou84, Cou85].

Conference [Boi97]. **Construct** [CH81]. **Construction** [Cou77]. **Continuation** [CPS89, CS90, CFS94]. **Convecting** [CG87]. **Convection** [GCS82, GCC88, GC84]. **Convective** [BPC+91]. **Coupled** [BGP+92, BCG94a, BCG94b]. **Current** [CGP92a]. **Current-Voltage** [CGP92a]. **Curves** [CRSM73].

Decomposition [BCG94a, BCG94b]. **Design** [CEK+89, CFS86]. **Development** [CFS86]. **Device** [BCF+86, BCD+89, BBC+90, BDR+94, CFG89, CS90, CJ90, CPS91, CFS94, CFS86, PCR+91, PBR+92, SCF+86, CPS89]. **Device-Circuit** [BDR+94]. **Devices** [BCF+85, BCPS92, BDR+94, CGP92a, SC94]. **Differential** [BCCS89]. **Diffusion** [BCF91]. **dimensional** [PBR+92]. **diminishing** [CGR86]. **Discrete** [Cou84, Cou85]. **Display** [CG92]. **Domain** [BCG94a, BCG94b]. **Drift** [BCF91]. **Drift-Diffusion** [BCF91]. **Dynamic** [CG91].

Editor [CG83]. **Effects** [BCPS92]. **Electrical** [LFC90]. **Element** [CFS94]. **Energy** [BPC+91, CRSM73]. **enhancement** [Boi97]. **Equation** [BCG+84]. **Equations** [BCCS89, BCG94a, BCG94b, BCF91, CRSM73, CFS94]. **Equations-of-motion** [CRSM73]. **Evaluation** [BPC+91]. **Extracting** [CFG89].

Factorization [BCCS89]. **Faster** [CS90]. **Fitting** [CFG89]. **Flows** [CG87, GCC88]. **Folds** [CGP92a]. **Formation** [CG87, GCS82, GC84]. **Fully** [BPC+91, BGP+92]. **Functions** [CG92].

Generation [CPS91]. **Gradient** [CFG89]. **Grid** [BCF91, CPS91]. **Grove** [CG83]. **Guide** [BCC+79].

HBTs [BPC+91, BGP+92]. **Hearing** [CG91]. **Hierarchical** [BCPS92]. **Hydrodynamic** [BPC+91, BGP+92]. **Hyperbolic** [Cou80, Cou84, Cou85].

IFIP [Boi97]. **II** [CCLW94]. **Incorporating** [CFS94]. **Inferno** [Cou97]. **Influence** [BPC+91]. **Initial** [Cou80, Cou84, Cou85]. **Initial-Boundary** [Cou80]. **Initial-Boundary-Value** [Cou84, Cou85]. **InP** [BGP+92]. **InP-based** [BGP+92]. **Instability** [BCG+84]. **Integrated** [PBR+92]. **Interpolating** [CH81]. **Iteration** [CJ90]. **Iterative** [BCD+89].

July [Boi97].

Kingdom [Boi97].

Language [GC83]. **Languages** [CG79]. **Large** [GCC88]. **Large-Cell** [GCC88]. **Latchup** [CPS88]. **Library** [BCC+79, CCGH80, Cou77]. **Loess** [CG91].

Macromodeling [CGR83]. **Mean** [GCC88]. **Meshes** [CS90]. **Method** [CRSM73]. **Methods** [BCD+89, CPS88, CPS89]. **Microelectronics** [CGP+92b]. **Mixed** [LFC90]. **Mixed-Mode** [LFC90]. **Mode** [LFC90]. **Model** [BPC+91, BCG+84]. **Modeling** [CS90, CG90b]. **Models** [CFS94]. **Modular** [CJ90]. **motion** [CRSM73].

NAPLUG [BCC+79]. **Near** [BCG+84, GCS82, GC84]. **Network** [Cou97]. **Network-based** [Cou97]. **Noncharacteristic** [Cou84, Cou85]. **Nonequilibrium** [BCPS92]. **Nonlinear** [GCS82, GC84]. **Note** [Cou77]. **Numerical** [BCG+84, BCC+79, CCGH80, Cou77, CG79, CG87, Boi97].

Object [LFC90]. **Object-Oriented** [LFC90]. **Onset**

[BCG+84, GCS82, GCC88, GC84]. **Oriented** [LFC90]. **Outer** [CJ90]. **Oxford** [Boi97].

Parallel [BCG94a, BCG94b]. **Part** [CJ90]. **Partial** [BCCS89]. **Parts** [CCLW94]. **Pattern** [CG87, GCS82, GC84]. **PDE** [BCPS92]. **Industry** [CEK+89]. **Philosophy** [CG89]. **Pine** [GC83]. **Polygons** [CG92]. **Potential** [CRSM73]. **Problems** [Cou80, Cou84, Cou85]. **Procedure** [BCCS89]. **proceedings** [Boi97]. **Process** [PBR+92]. **Program** [BCC+79, Cou77]. **Programming** [GC83]. **Progress** [BBC+90].

Quality [Boi97].

Rayleigh [BCG+84, GCS82, GC84]. **Rayleigh-Bénard** [BCG+84, GCS82, GC84]. **Refinement** [BCF91].

Scientific [CG89, CG90a, CG90c, Cou97]. **Seeing** [CG91]. **Semiconductor** [BCD+89, BBC+90, BCPS92, BDR+94, CJ90, CGP92a, SCF+86, SC94, CPS89]. **Semiconductors** [CCLW94]. **Shaded** [CG92]. **Sight** [CG90a]. **Silicon** [BCF+85, CG90b, PCR+91]. **Simulation** [BCF+85, BCF+86, BCD+89, BBC+90, BGP+92, BCPS92, BDR+94, CPS88, CJ90, CPS91, CFS94, LFC90, PCR+91, PBR+92, SCF+86, CGR86, CPS89]. **Simulations** [CFG89, SC94]. **Software** [CG79, CEK+89, Boi97]. **Solution** [BCG+84, Cou80]. **Some** [SCF+86]. **Sound** [CG90a, CG92]. **Space** [CG92]. **Spatial** [CS90]. **Splines** [CH81, CGR86]. **State** [CPS88]. **Steady** [CPS88]. **Steady-State** [CPS88]. **Strategy** [BCF91]. **Studies** [CG87, CG90b]. **Submicron** [PBR+92]. **Supercomputers** [CFS86]. **Support** [CCGH80]. **Surfaces** [CG91]. **Systems** [BCCS89].

TC2 [Boi97]. **TC2/WG2.5** [Boi97]. **Techniques** [CG90c]. **Technology** [CFS86, PBR+92]. **Thermal** [BGP+92]. **Three** [CG92, PBR+92]. **Three-dimensional** [PBR+92]. **Time** [CG92]. **Tools** [CG89]. **Transient** [BCF+85, BCF+86, CJ90]. **Transistor** [CFG89]. **Transistors** [PBR+92]. **Transport** [BCPS92, BCG94a, BCG94b].

ULSI [PCR+91, SC94]. **United** [Boi97]. **University** [CEK+89]. **University/ Industry** [CEK+89]. **User** [BCC+79]. **Using** [BPC+91, CG92, PBR+92, CS90].

Value [Cou80, Cou84, Cou85]. **Variables** [CG92]. **Variation** [CGR86]. **via** [Cou97]. **Video** [CG90a]. **VLSI** [CPS91, CFS86]. **Voltage** [CGP92a].

WG2.5 [Boi97]. **Working** [Boi97].

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